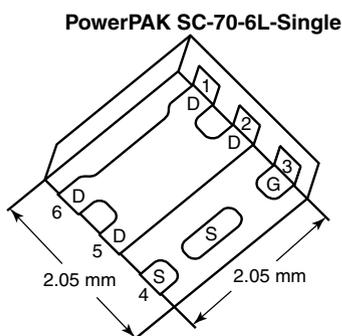




P-Channel 12 V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω) (Max.)	I _D (A)	Q _g (Typ.)
- 12	0.0135 at V _{GS} = - 4.5 V	- 12 ^a	31 nC
	0.0194 at V _{GS} = - 2.5 V	- 12 ^a	
	0.0344 at V _{GS} = - 1.8 V	- 12 ^a	
	0.0710 at V _{GS} = - 1.5 V	- 3	



Ordering Information:
[SiA447DJ-T4-GE3](#) (Lead (Pb)-free and Halogen-free)
[SiA447DJ-T1-GE3](#) (Lead (Pb)-free and Halogen-free)

FEATURES

- TrenchFET[®] Power MOSFET
- Thermally Enhanced PowerPAK[®] SC-70 Package
 - Small Footprint Area
 - Low On-Resistance
- 100 % R_g Tested
- Material categorization:
For definitions of compliance please see www.vishay.com/doc?99912

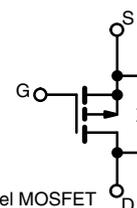
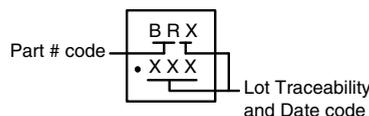


RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Providing low voltage drop in Smart Phones, Tablet PCs, Mobile Computing:
 - Battery Switches
 - Battery Management
 - Load Switches

Marking Code



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	- 12	V
Gate-Source Voltage	V _{GS}	± 8	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	- 12 ^a
		T _C = 70 °C	- 12 ^a
		T _A = 25 °C	- 12 ^{a, b, c}
		T _A = 70 °C	- 10 ^{b, c}
Pulsed Drain Current (t = 300 μs)	I _{DM}	- 50	A
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	
		T _A = 25 °C	- 2.9 ^{b, c}
Maximum Power Dissipation	P _D	T _C = 25 °C	19
		T _C = 70 °C	12
		T _A = 25 °C	3.5 ^{b, c}
		T _A = 70 °C	2.2 ^{b, c}
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R _{thJA}	28	36	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	5.3	6.5	

Notes:

- Package limited
- Surface mounted on 1" x 1" FR4 board.
- t = 5 s.
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 80 °C/W.



SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0, I _D = - 250 μA	- 12			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = - 250 μA		- 7		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			3		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 0.4		- 0.85	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 8 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 12 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 12 V, V _{GS} = 0 V, T _J = 55 °C			- 10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≤ - 5 V, V _{GS} = - 4.5 V	- 10			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 7 A		0.0110	0.0135	Ω
		V _{GS} = - 2.5 V, I _D = - 5 A		0.0150	0.0194	
		V _{GS} = - 1.8 V, I _D = - 3 A		0.0230	0.0344	
		V _{GS} = - 1.5 V, I _D = - 1 A		0.0400	0.0710	
Forward Transconductance ^a	g _{fs}	V _{DS} = - 6 V, I _D = - 7 A		35		S
Dynamic^b						
Input Capacitance	C _{iss}	V _{DS} = - 6 V, V _{GS} = 0 V, f = 1 MHz		2880		pF
Output Capacitance	C _{oss}			590		
Reverse Transfer Capacitance	C _{rss}			585		
Total Gate Charge	Q _g	V _{DS} = - 6 V, V _{GS} = - 8 V, I _D = - 13 A		52	80	nC
				31	47	
Gate-Source Charge	Q _{gs}	V _{DS} = - 6 V, V _{GS} = - 4.5 V, I _D = - 13 A		4.2		
Gate-Drain Charge	Q _{gd}			7.8		
Gate Resistance	R _g	f = 1 MHz	0.8	4.3	8.6	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 6 V, R _L = 0.6 Ω I _D ≅ - 10 A, V _{GEN} = - 4.5 V, R _g = 1 Ω		30	60	ns
Rise Time	t _r			30	60	
Turn-Off Delay Time	t _{d(off)}			60	120	
Fall Time	t _f			25	50	
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 6 V, R _L = 0.6 Ω I _D ≅ - 10 A, V _{GEN} = - 8 V, R _g = 1 Ω		12	25	
Rise Time	t _r			10	20	
Turn-Off Delay Time	t _{d(off)}			65	130	
Fall Time	t _f			20	40	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 12	A
Pulse Diode Forward Current	I _{SM}				- 50	
Body Diode Voltage	V _{SD}	I _S = - 10 A, V _{GS} = 0		- 0.8	- 1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = - 10 A, di/dt = 100 A/μs, T _J = 25 °C		25	50	ns
Body Diode Reverse Recovery Charge	Q _{rr}			7.5	15	nC
Reverse Recovery Fall Time	t _a			8		ns
Reverse Recovery Rise Time	t _b			17		

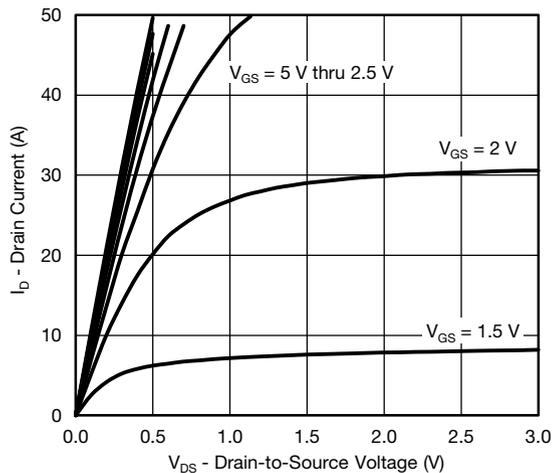
Notes:

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

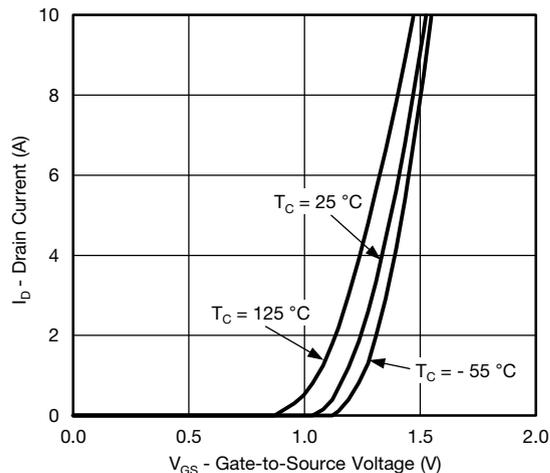
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



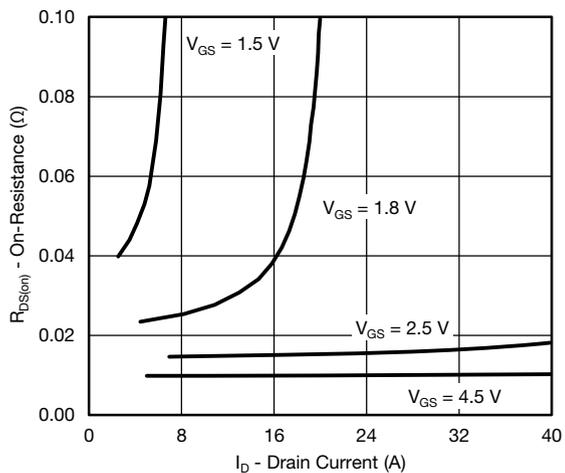
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



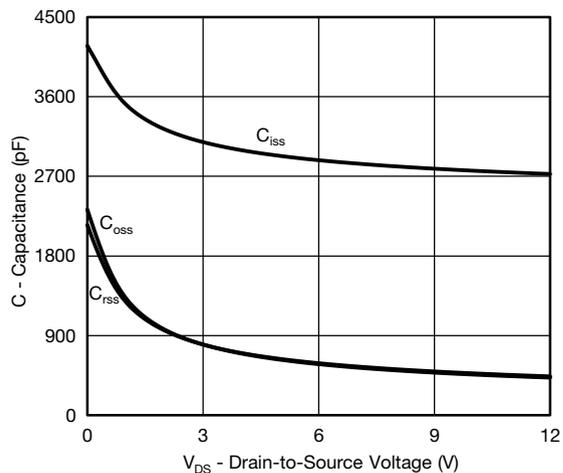
Output Characteristics



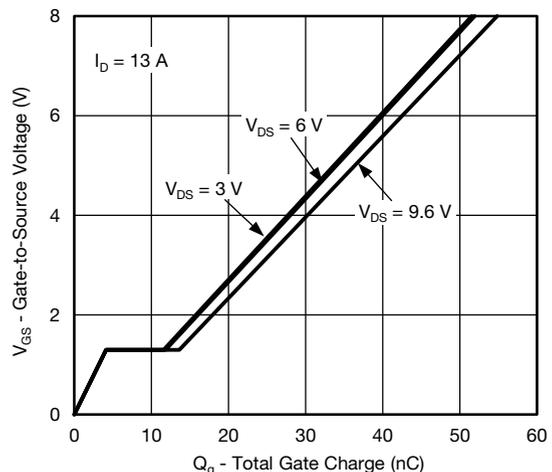
Transfer Characteristics



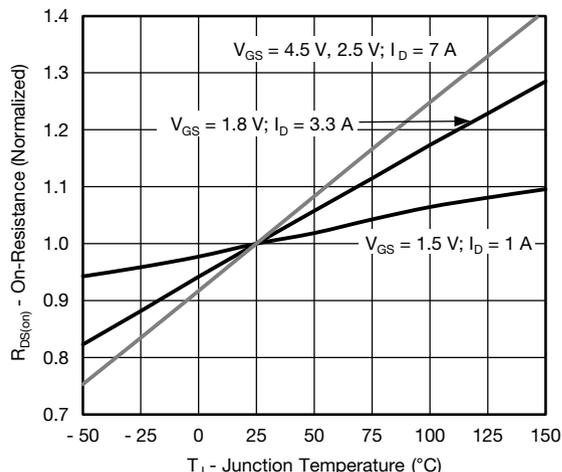
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



Gate Charge



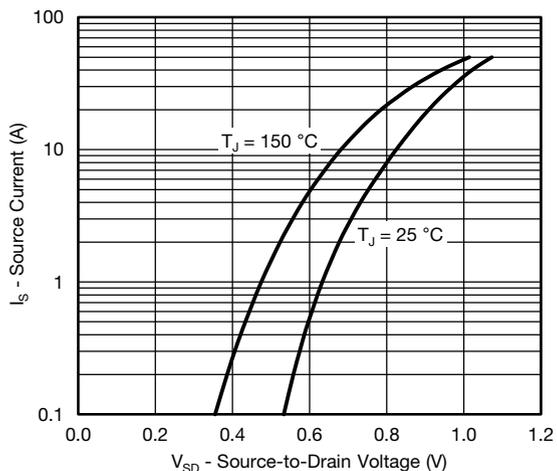
On-Resistance vs. Junction Temperature

SiA447DJ

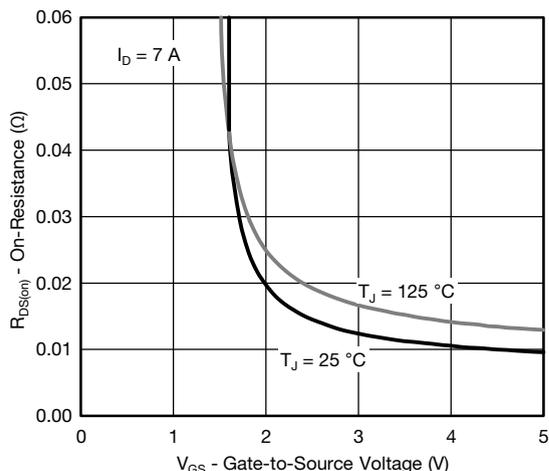
Vishay Siliconix



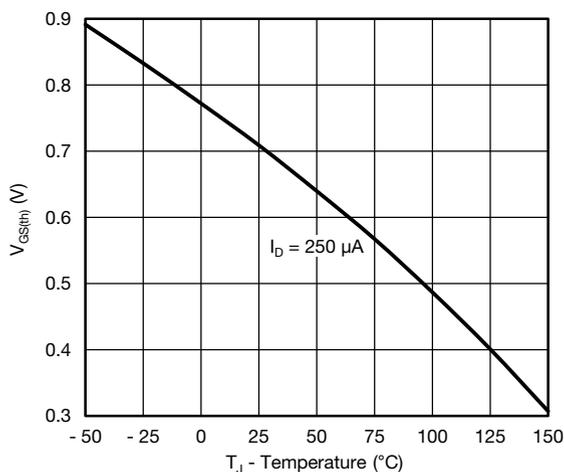
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



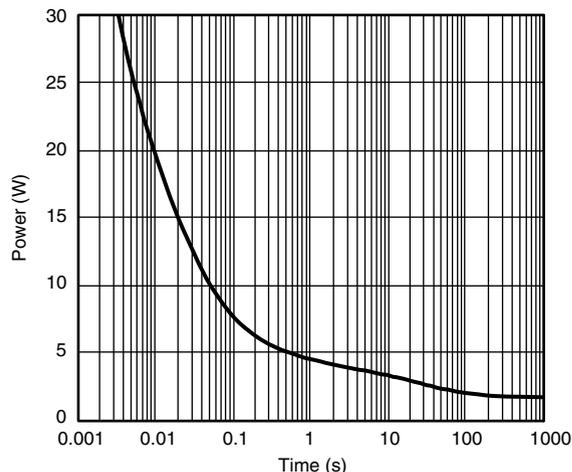
Source-Drain Diode Forward Voltage



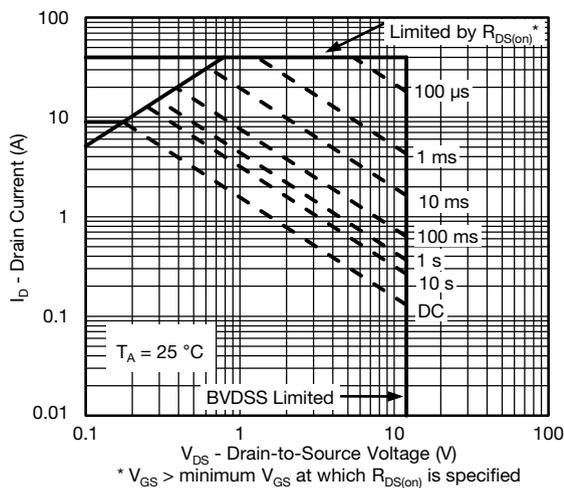
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



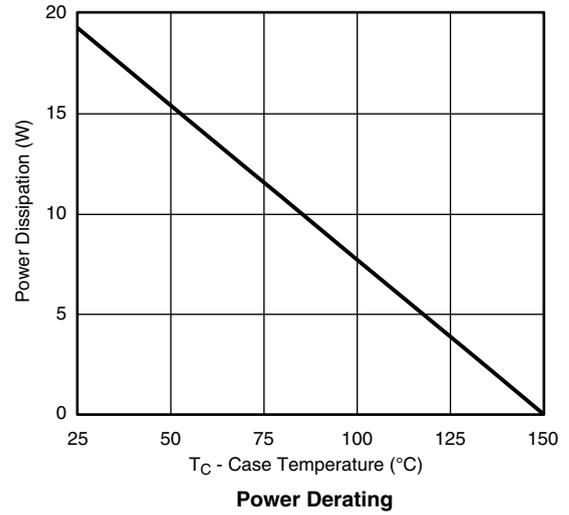
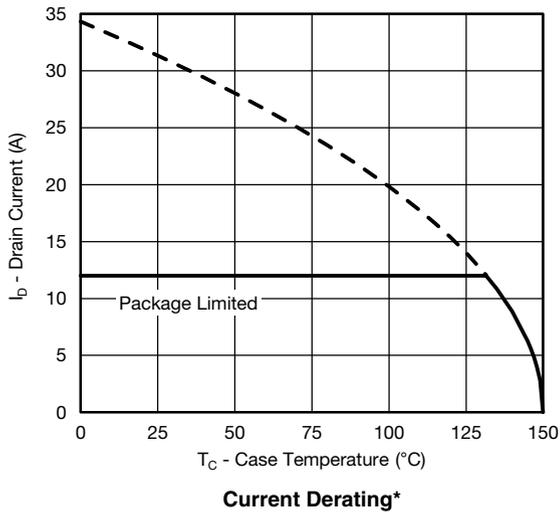
Single Pulse Power, Junction-to-Ambient



Safe Operating Area, Junction-to-Ambient



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



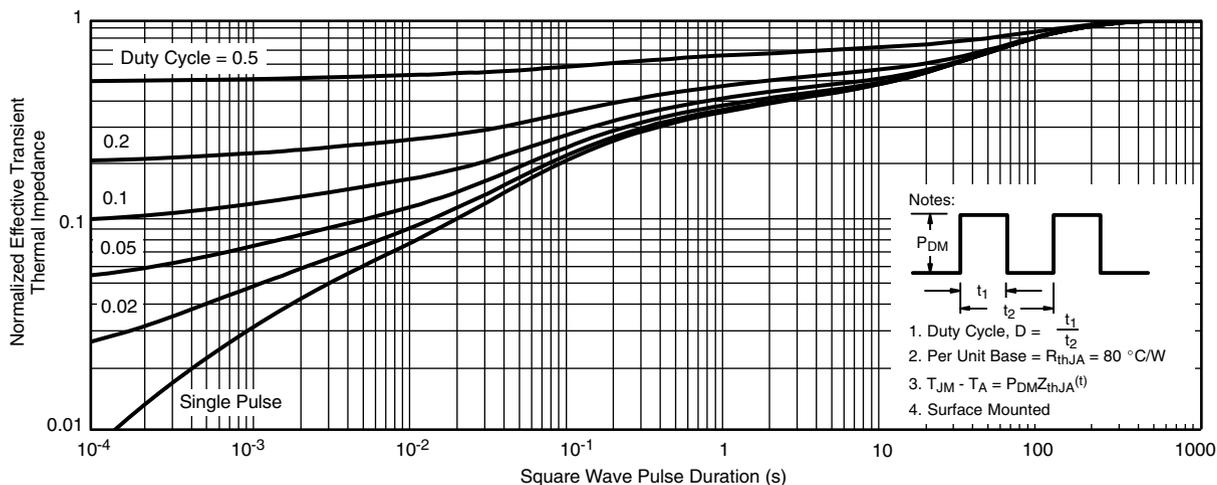
* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

SiA447DJ

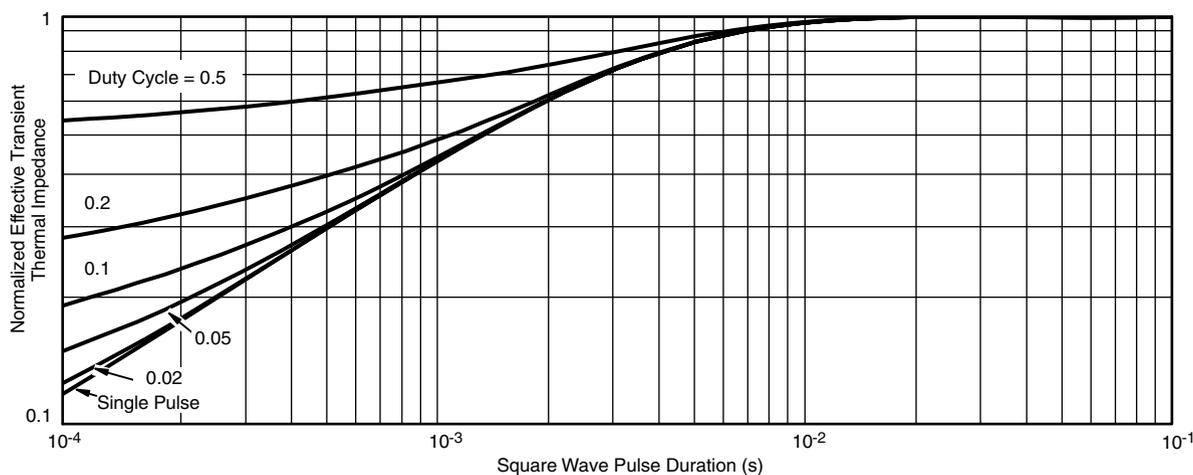
Vishay Siliconix



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

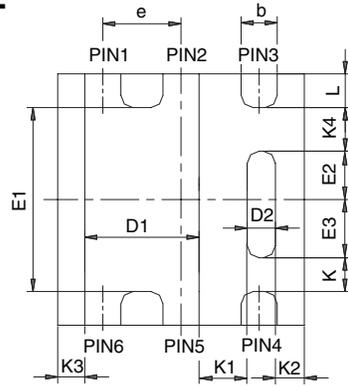


Normalized Thermal Transient Impedance, Junction-to-Case

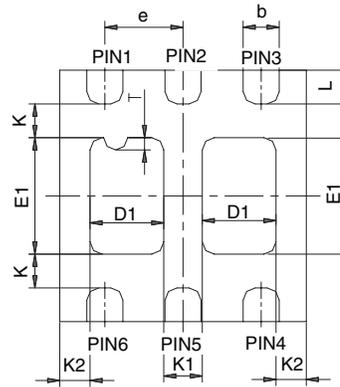
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63774.



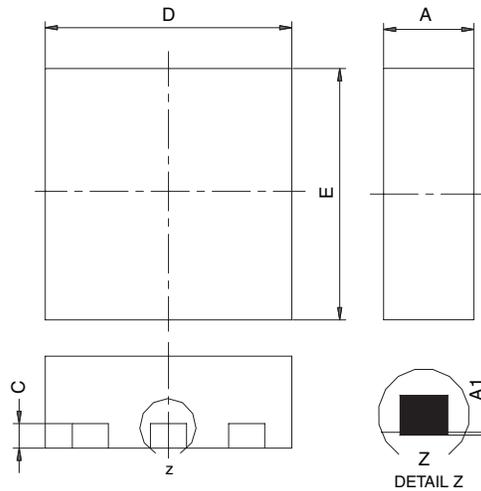
PowerPAK® SC70-6L



BACKSIDE VIEW OF SINGLE



BACKSIDE VIEW OF DUAL



- Notes:
 1. All dimensions are in millimeters
 2. Package outline exclusive of mold flash and metal burr
 3. Package outline inclusive of plating

DIM	SINGLE PAD						DUAL PAD					
	MILLIMETERS			INCHES			MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
A	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
C	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D2	0.135	0.235	0.335	0.005	0.009	0.013						
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E2	0.345	0.395	0.445	0.014	0.016	0.018						
E3	0.425	0.475	0.525	0.017	0.019	0.021						
e	0.65 BSC			0.026 BSC			0.65 BSC			0.026 BSC		
K	0.275 TYP			0.011 TYP			0.275 TYP			0.011 TYP		
K1	0.400 TYP			0.016 TYP			0.320 TYP			0.013 TYP		
K2	0.240 TYP			0.009 TYP			0.252 TYP			0.010 TYP		
K3	0.225 TYP			0.009 TYP								
K4	0.355 TYP			0.014 TYP								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
T							0.05	0.10	0.15	0.002	0.004	0.006

ECN: C-07431 – Rev. C, 06-Aug-07
 DWG: 5934



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Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

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<http://moschip.ru/get-element>

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